

1. Scope

The present specifications shall apply to an FMB-G16L.

2. Outline

Type	Silicon Schottky Barrier Diode
Structure	Resin Molded Flammability : UL94V-0(Equivalent)
Applications	High Frequency Rectification

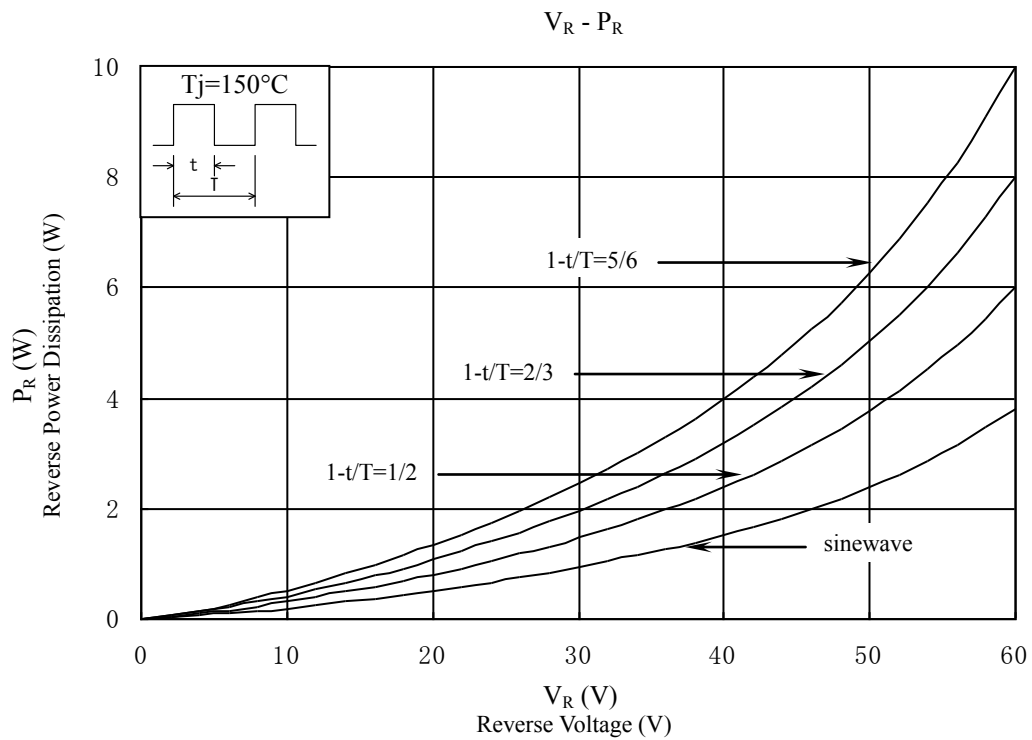
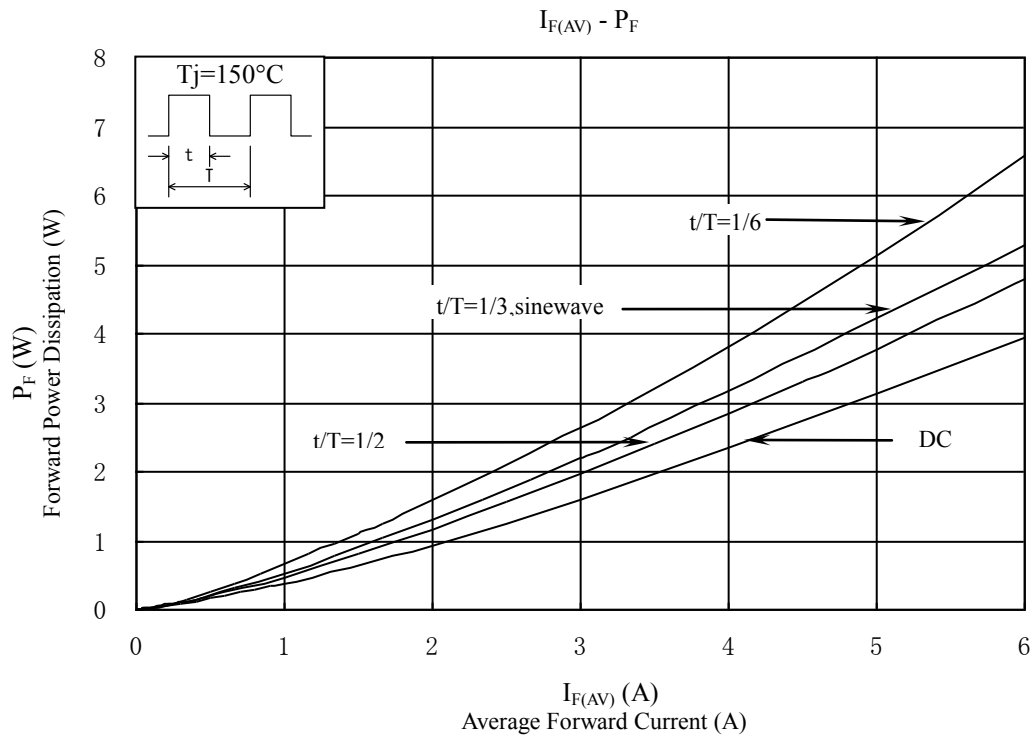
3. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	60	
2	Peak Reverse Voltage	V_{RM}	V	60	
3	Average Forward Current	$I_{F(AV)}$	A	6.0	Refer Derating of 6
4	Peak Surge Forward Current	I_{FSM}	A	50	10msec. half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	12.5	1msec $\leq t \leq$ 10msec
6	Junction Temperature	T_j	$^{\circ}C$	-40~+150	
7	Storage Temperature	T_{stg}	$^{\circ}C$	-40~+150	

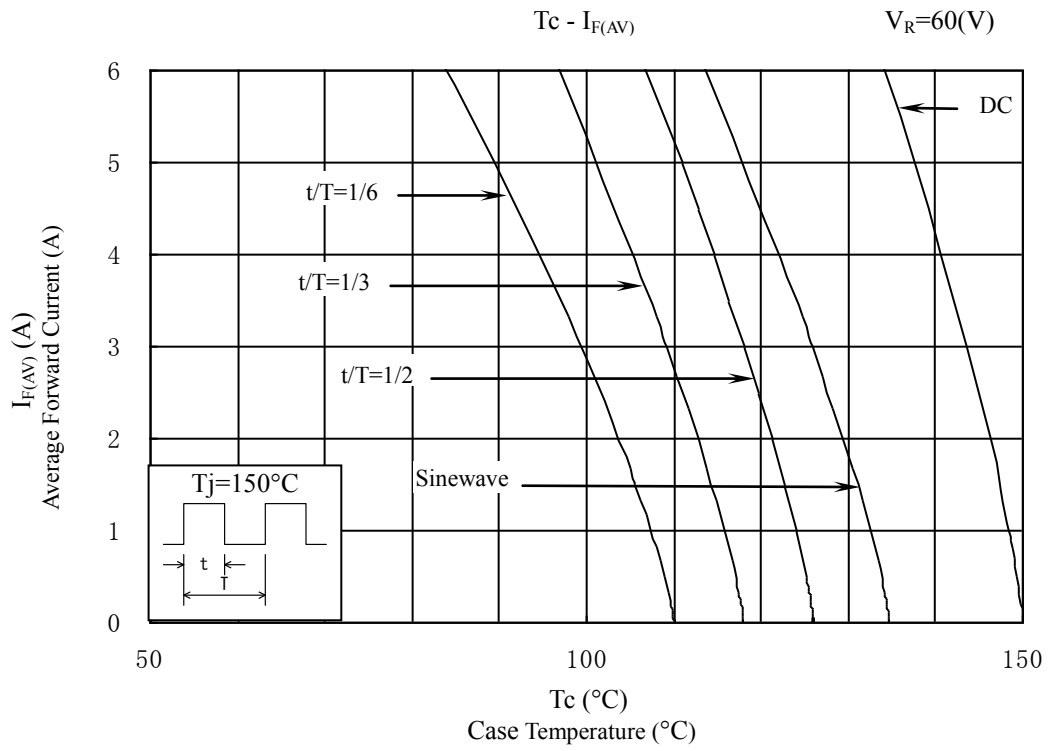
4. Electrical characteristics (Ta=25°C, unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	0.72 max.	$I_F=6.0A$
2	Reverse Leakage Current	I_R	mA	5.0 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	200 max.	$V_R=V_{RM}, T_j=150^{\circ}C$
4	Thermal Resistance	$R_{th(j-c)}$	$^{\circ}C/W$	4.0 max.	Between Junction and case

5. Characteristics

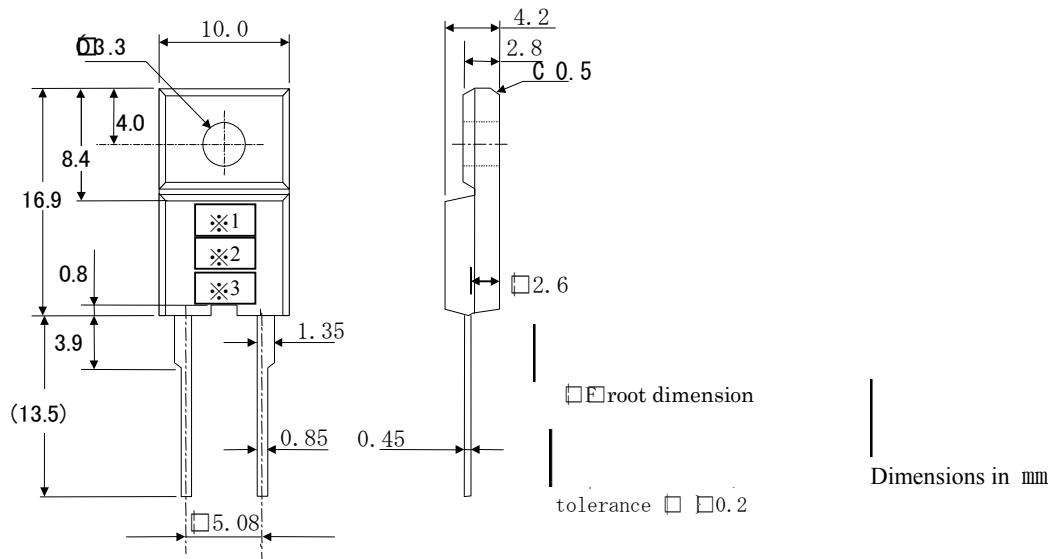


6. Derating



7. Package information

7-1 Package type, physical dimensions and material



7-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

7-3 Marking

Type Name	Marking		
	*1 Type Name	*2 Polarity	*3 Lot number
FMB-G16L	FMBG16	L	1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 4128 (Jan. 28, 2004)